## 2SD1135

## Silicon NPN Triple Diffused

# **HITACHI**

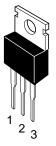
ADE-208-906 (Z) 1st. Edition Sep. 2000

#### **Application**

Low frequency power amplifier complementary pair with 2SB859

#### **Outline**

TO-220AB



- 1. Base
- 2. Collector (Flange)
- 3. Emitter

## **Absolute Maximum Ratings** (Ta = 25°C)

Item	Symbol	Ratings	Unit
Collector to base voltage	$V_{\text{CBO}}$	100	V
Collector to emitter voltage	V <sub>CEO</sub>	80	V
Emitter to base voltage	$V_{EBO}$	5	V
Collector current	I <sub>c</sub>	4	А
Collector peak current	I <sub>C(peak)</sub>	8	А
Collector power dissipation	P <sub>c</sub> *1	40	W
Junction temperature	Tj	150	°C
Storage temperature	Tstg	-45 to +150	°C

Note: 1. Value at  $T_c = 25^{\circ}C$ .



### 2SD1135

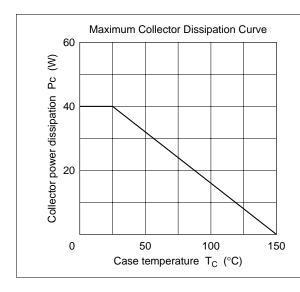
### **Electrical Characteristics** (Ta = 25°C)

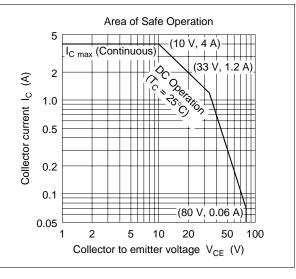
Item	Symbol	Min	Тур	Max	Unit	Test conditions
Collector to emitter breakdown voltage	$V_{(BR)CEO}$	80	_	_	V	$I_{\rm C}$ = 50 mA, $R_{\rm BE}$ = $\infty$
Emitter to base breakdown voltage	$V_{(BR)EBO}$	5	_	_	V	$I_{E} = 10  \mu A,  I_{C} = 0$
Collector cutoff current	I <sub>CBO</sub>		_	0.1	mA	V <sub>CB</sub> = 80 V, I <sub>E</sub> = 0
DC current transfer ratio	h <sub>FE1</sub> *1	60	_	200		$V_{CE} = 5 \text{ V}, I_{C} = 1 \text{ A}^{*2}$
	$h_{\text{FE2}}$	35	_	_		$V_{CE} = 5 \text{ V}, I_{C} = 0.1 \text{ A}^{*2}$
Base to emitter voltage	$V_{\text{BE}}$	_		1.5	V	$V_{CE} = 5 \text{ V}, I_{C} = 1 \text{ A}^{*2}$
Collector to emitter saturation voltage	$\boldsymbol{V}_{\text{CE(sat)}}$	_	_	2	V	$I_{\rm C} = 2 \text{ A}, I_{\rm B} = 0.2 \text{ A}^{*2}$
Gain bandwidth product	f <sub>T</sub>	_	10	_	MHz	$V_{CE} = 5 \text{ V}, I_{C} = 0.5 \text{ A}^{*2}$
Collector output capacitance	Cob	_	40	_	pF	$V_{CB} = 20 \text{ V}, I_{E} = 0, f = 1 \text{ MHz}$

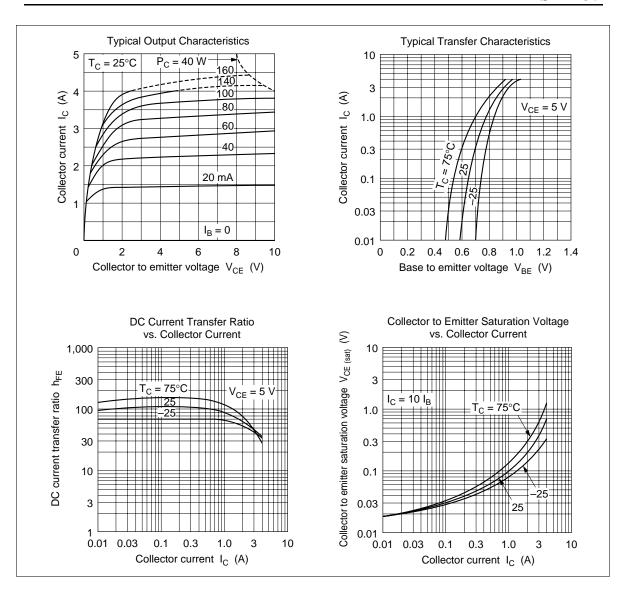
Notes: 1. The 2SD1135 is grouped by  $h_{\text{FE1}}$  as follows.

2. Pulse test.

В	С
60 to 120	100 to 200

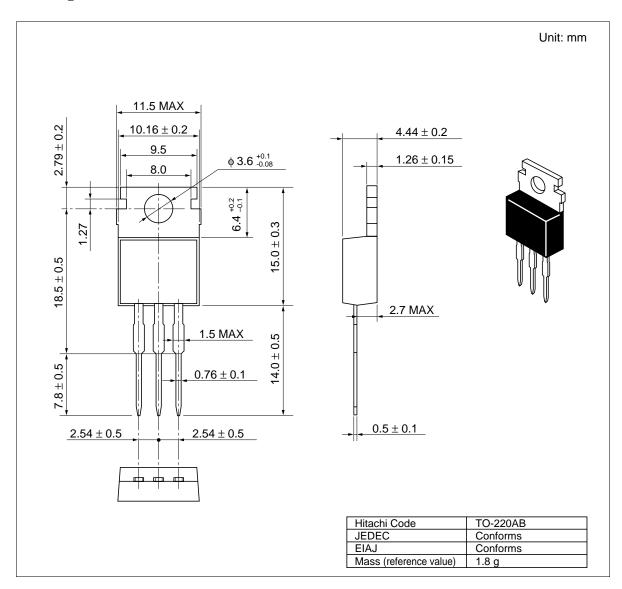






### 2SD1135

### **Package Dimensions**



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